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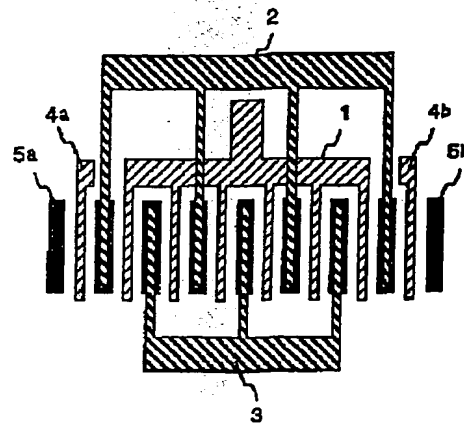
(54) **SEMICONDUCTOR DEVICE, MANUFACTURE
THEREOF, AND TELECOMMUNICATION
EQUIPMENT**

(57) Abstract:

PROBLEM TO BE SOLVED: To reduce fluctuations in the threshold of each gate finger and to improve current shielding characteristics near the threshold by isolating gate fingers at both ends of a plurality of gate fingers from the other gate fingers that are connected by a gate electrode.

SOLUTION: In a field effect transistor(FET) having a plurality of gate fingers, gate fingers 4a and 4b at both ends are isolated from the other gate fingers connected by a gate electrode 1. In this case, at least two gate fingers are isolated at each end. As a result, the controllability of drain current by gate voltage can be improved, and current shielding characteristic near the threshold can be improved, and hence the high frequency characteristics of a semiconductor device can be improved.

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